



## HiPerFRED™ Epitaxial Diode with soft recovery

$V_{RSM}$ V	$V_{RRM}$ V	Type	Marking on product
600	600	DSEP 6-06AS	6P060AS

$I_{FAVM} = 6 \text{ A}$   
 $V_{RRM} = 600 \text{ V}$   
 $t_{rr} = 20 \text{ ns}$



TO-252AA (DPAK)



Symbol	Conditions	Maximum Ratings			Features
$I_{FRMS}$	$T_{VJ} = T_{VJM}$	26		A	
$I_{FAVM}$ ①	$T_c = 152^\circ\text{C}$ ; rectangular, $d = 0.5$	6		A	
$I_{FRM}$	$t_p < 10 \mu\text{s}$ ; rep. rating, pulse width limited by $T_{VJM}$	12		A	
$I_{FSM}$	$T_{VJ} = 45^\circ\text{C}$ ; $t = 10 \text{ ms}$	(50 Hz), sine		40	
$E_{AS}$	$T_{VJ} = 25^\circ\text{C}$ ; non-repetitive $I_{AS} = 0.8 \text{ A}$ ; $L = 180 \mu\text{H}$	0.1		mJ	
$I_{AR}$	$V_A = 1.5 \cdot V_R$ typ.; $f = 10 \text{ kHz}$ ; repetitive	0.1		A	
$T_{VJ}$		-40...+175		°C	
$T_{VJM}$		175		°C	
$T_{stg}$		-40...+150		°C	
$P_{tot}$	$T_c = 25^\circ\text{C}$	55		W	
Weight	typ.	0.3		g	

Symbol	Conditions	Characteristic Values		
		typ.	max.	
$I_R$	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 150^\circ\text{C}$ $V_R = V_{RRM}$	50		μA
		0.2		mA
$V_F$	$I_F = 6 \text{ A}$ ; $T_{VJ} = 150^\circ\text{C}$ $T_{VJ} = 25^\circ\text{C}$	1.33		V
		2.02		V
$R_{thJC}$		2.8		K/W
$t_{rr}$	$I_F = 1 \text{ A}$ ; $-di/dt = 200 \text{ A}/\mu\text{s}$ ; $V_R = 30 \text{ V}$ ; $T_{VJ} = 25^\circ\text{C}$	20	tbd	ns
$I_{RM}$	$V_R = 100 \text{ V}$ ; $I_F = 10 \text{ A}$ ; $-di_F/dt = 100 \text{ A}/\mu\text{s}$ $T_{VJ} = 100^\circ\text{C}$	3.5	4.4	A

①  $I_{FAVM}$  rating includes reverse blocking losses at  $T_{VJM}$ ,  $V_R = 0.6 V_{RRM}$ , duty cycle  $d = 0.5$

Data according to IEC 60747

### Applications

- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

### Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses
- Operating at lower temperature or space saving by reduced cooling

Dimensions see pages D4 - 85-86

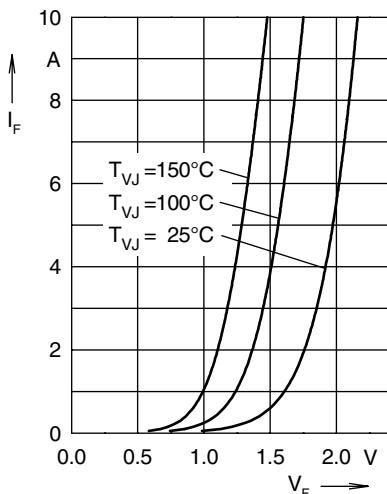


Fig. 1 Forward current  $I_F$  versus  $V_F$

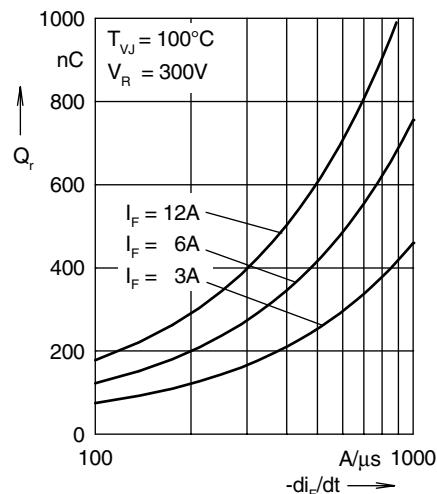


Fig. 2 Reverse recovery charge  $Q_r$  versus  $-di_F/dt$

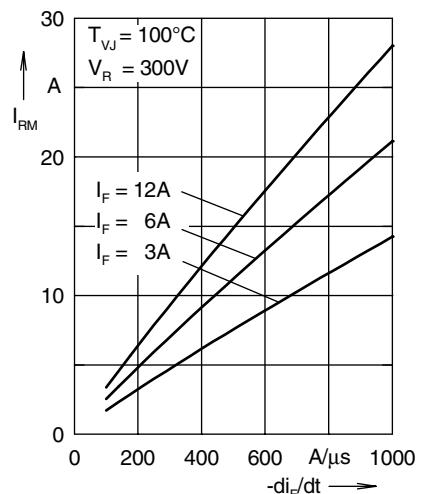


Fig. 3 Peak reverse current  $I_{RM}$  versus  $-di_F/dt$

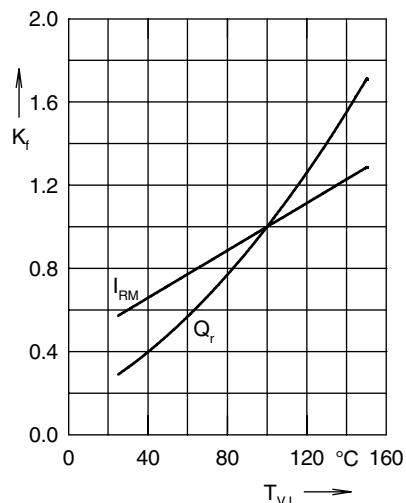


Fig. 4 Dynamic parameters  $Q_r$ ,  $I_{RM}$  versus  $T_{VJ}$

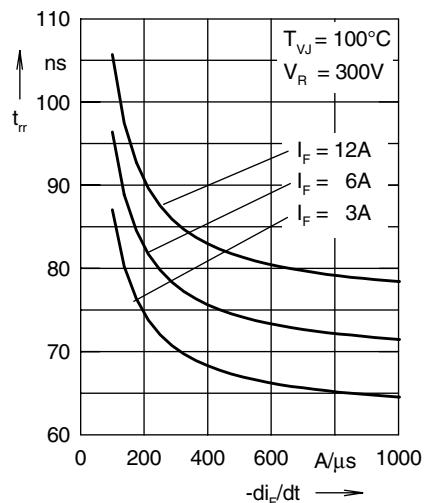


Fig. 5 Recovery time  $t_{rr}$  versus  $-di_F/dt$

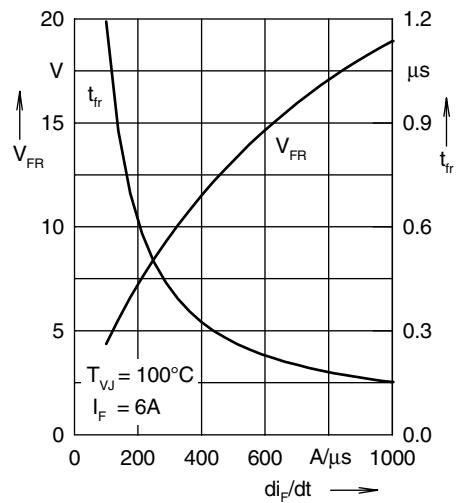


Fig. 6 Peak forward voltage  $V_{FR}$  and  $t_{fr}$  versus  $di_F/dt$

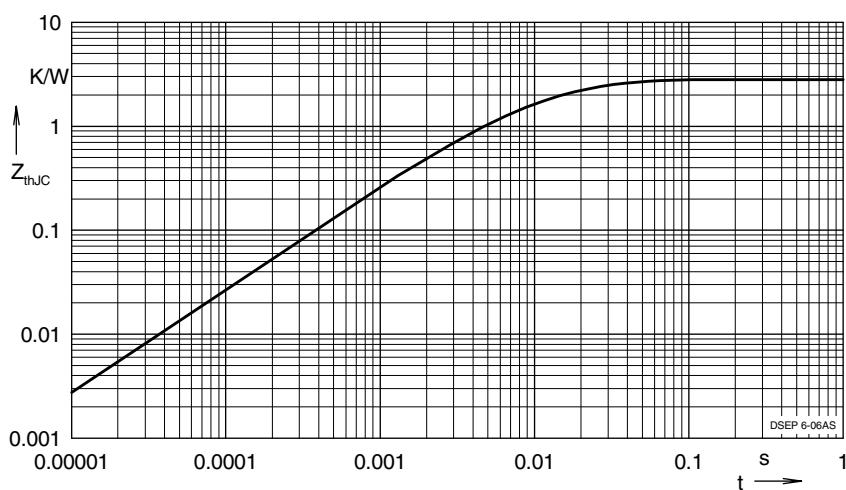


Fig. 7 Transient thermal resistance junction to case

NOTE: Fig. 2 to Fig. 6 shows typical values